

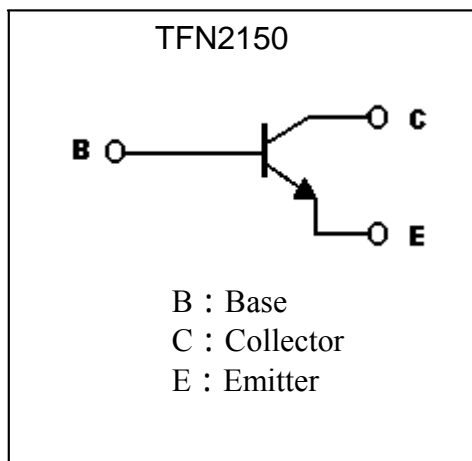
TFN2150

50V 4A NPN TRANSISTOR

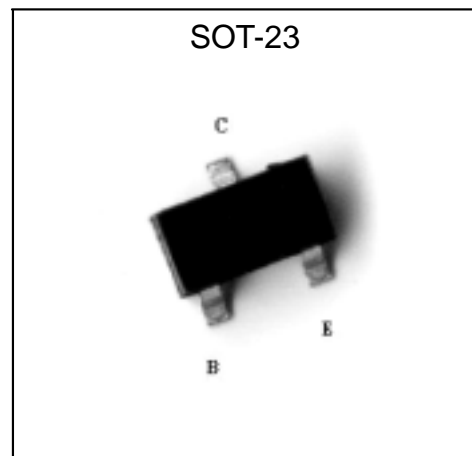
Features

- Low $V_{CE(sat)}$, typically 0.25V at $I_C / I_B = 2A / 0.1A$
- Excellent current gain characteristics
- Complementary to TFN1424
- Pb-free package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	4	A
Collector Current (Pulse)	I_{CP}	7 (Note 1)	A
Power Dissipation	P_d	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Note : 1. Single Pulse P_w 350 μ s, Duty 2%.



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	60	-	-	V	I _C =100μA, I _E =0
BV _{CEO}	50	-	-	V	I _C =1mA, I _B =0
BV _{EBO}	6	-	-	V	I _E =50μA, I _C =0
I _{CBO}	-	-	100	nA	V _{CB} =40V, I _E =0
I _{EBO}	-	-	100	nA	V _{EB} =5V, I _C =0
*V _{CE(sat)}	-	-	0.3	V	I _C =400mA, I _B =20mA
*V _{CE(sat)}	-	0.25	0.5	V	I _C =2A, I _B =100mA
*V _{BE(sat)}	-	-	1.5	V	I _C =2A, I _B =200mA
*h _{FE1}	200	-	-	-	V _{CE} =2V, I _C =100mA
*h _{FE2}	270	-	820	-	V _{CE} =2V, I _C =500mA
*h _{FE3}	100	-	-	-	V _{CE} =2V, I _C =1A
f _T	-	90	-	MHz	V _{CE} =5V, I _C =0.1A, f=100MHz
Cob	-	45	-	pF	V _{CB} =10V, f=1MHz

*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of hFE 2

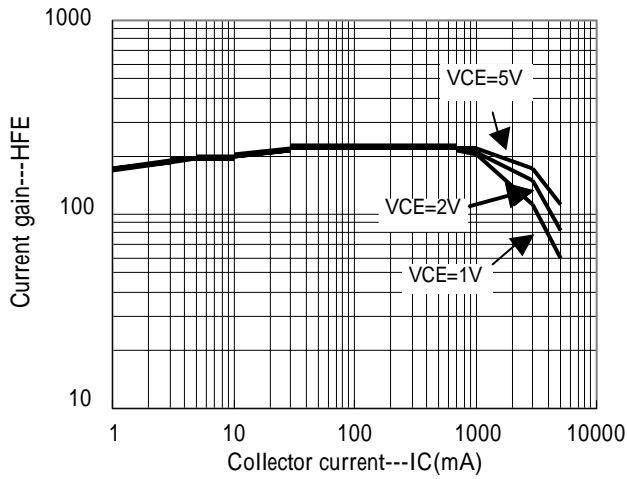
Rank	S	T
Range	270~560	390~820

Ordering Information

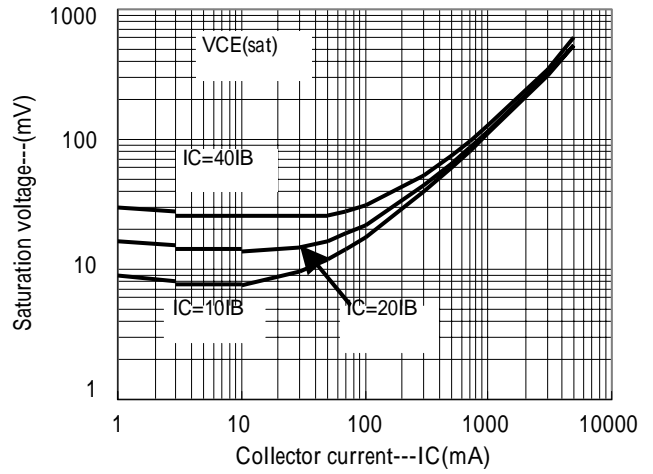
Device	Package	Shipping	Marking
TFN2150	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	CF

Characteristic Curves

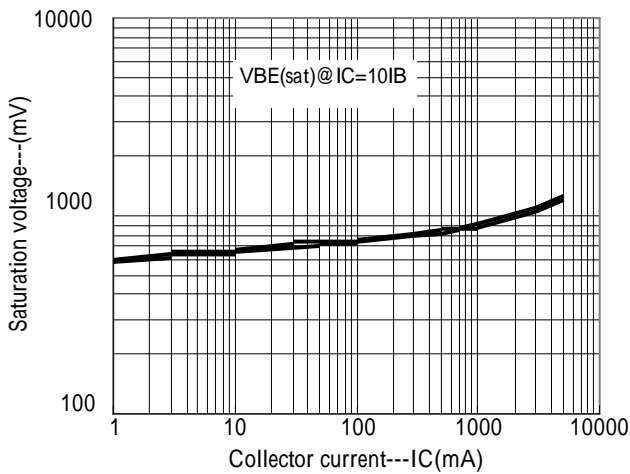
Current gain vs Collector current



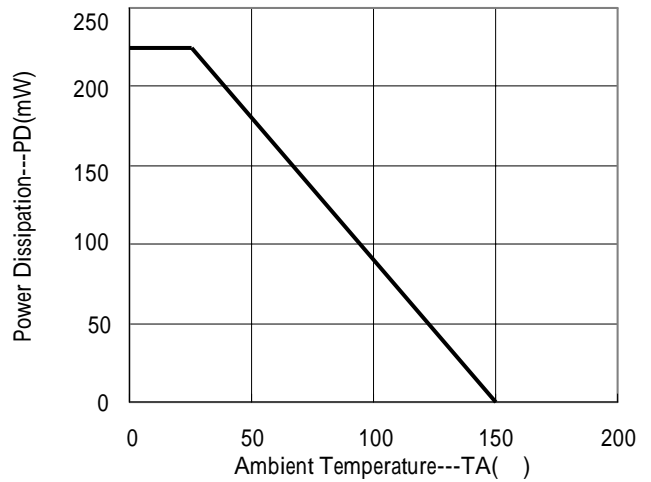
Saturation voltage vs Collector current



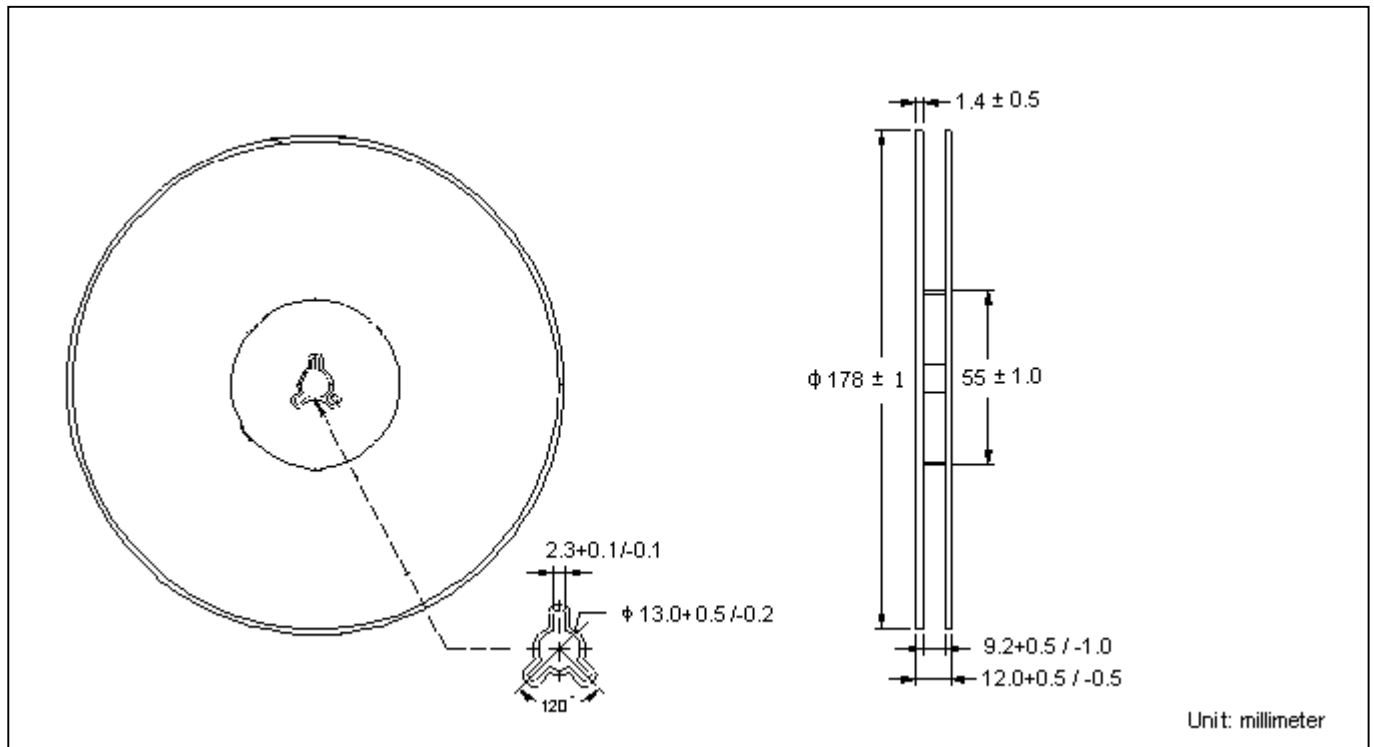
Saturation voltage vs Collector current



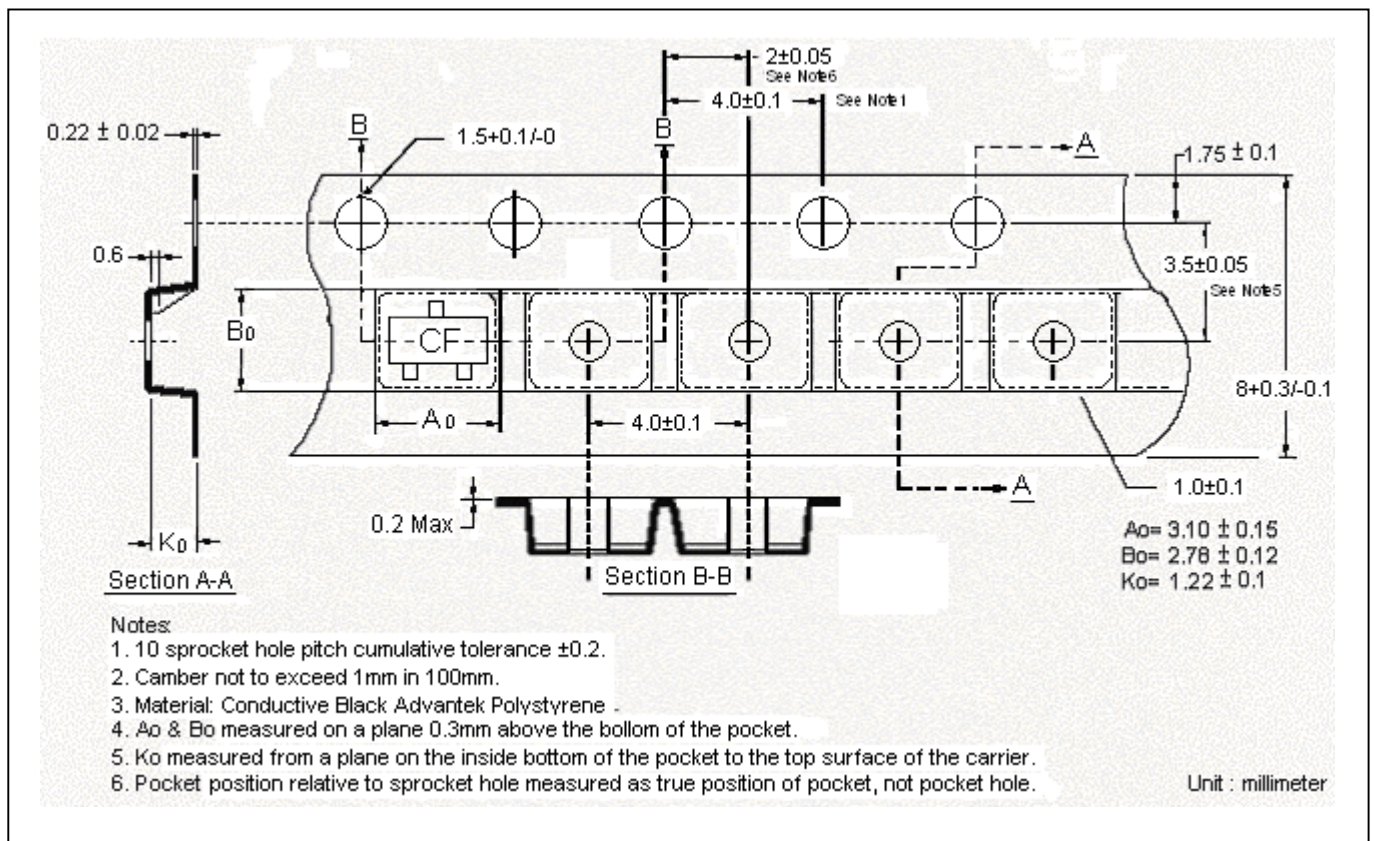
Power Derating Curve



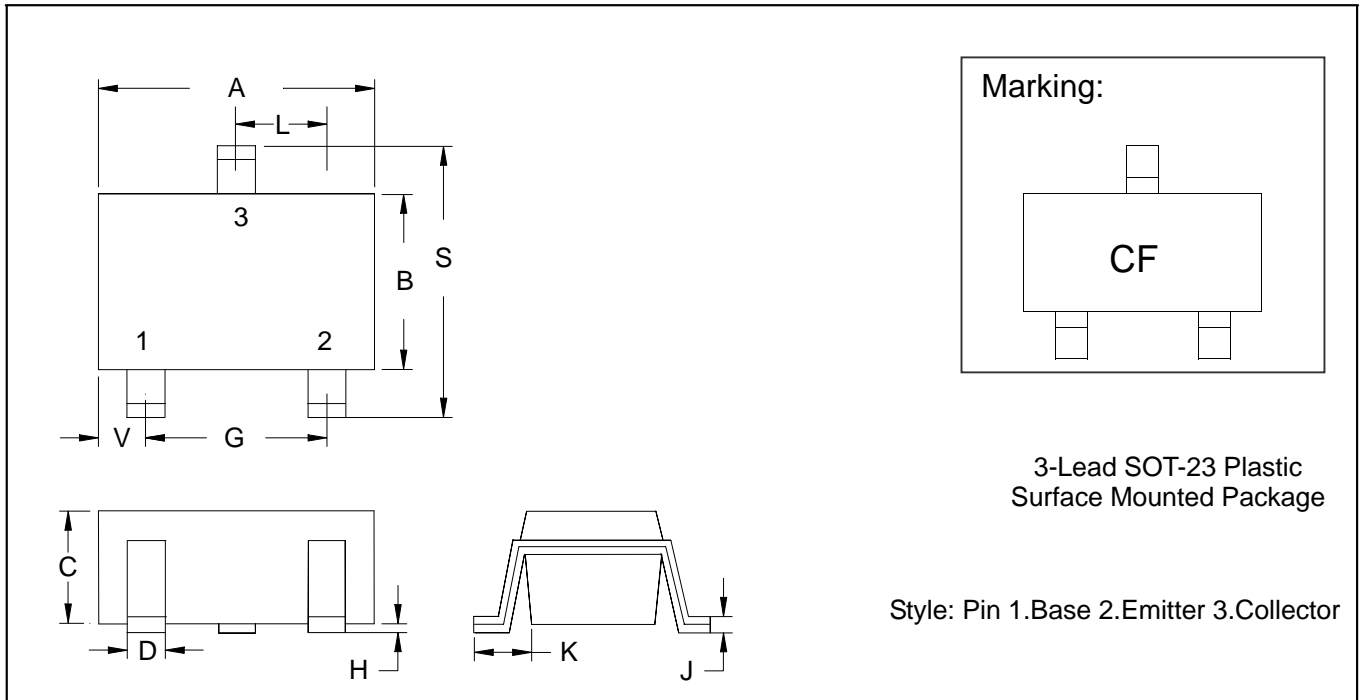
Reel Dimension



Carrier Tape Dimension



SOT-23 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local Tin Far sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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